



Advanced High Voltage Isolated Gate Driver for IGBT and SiC MOSFETs

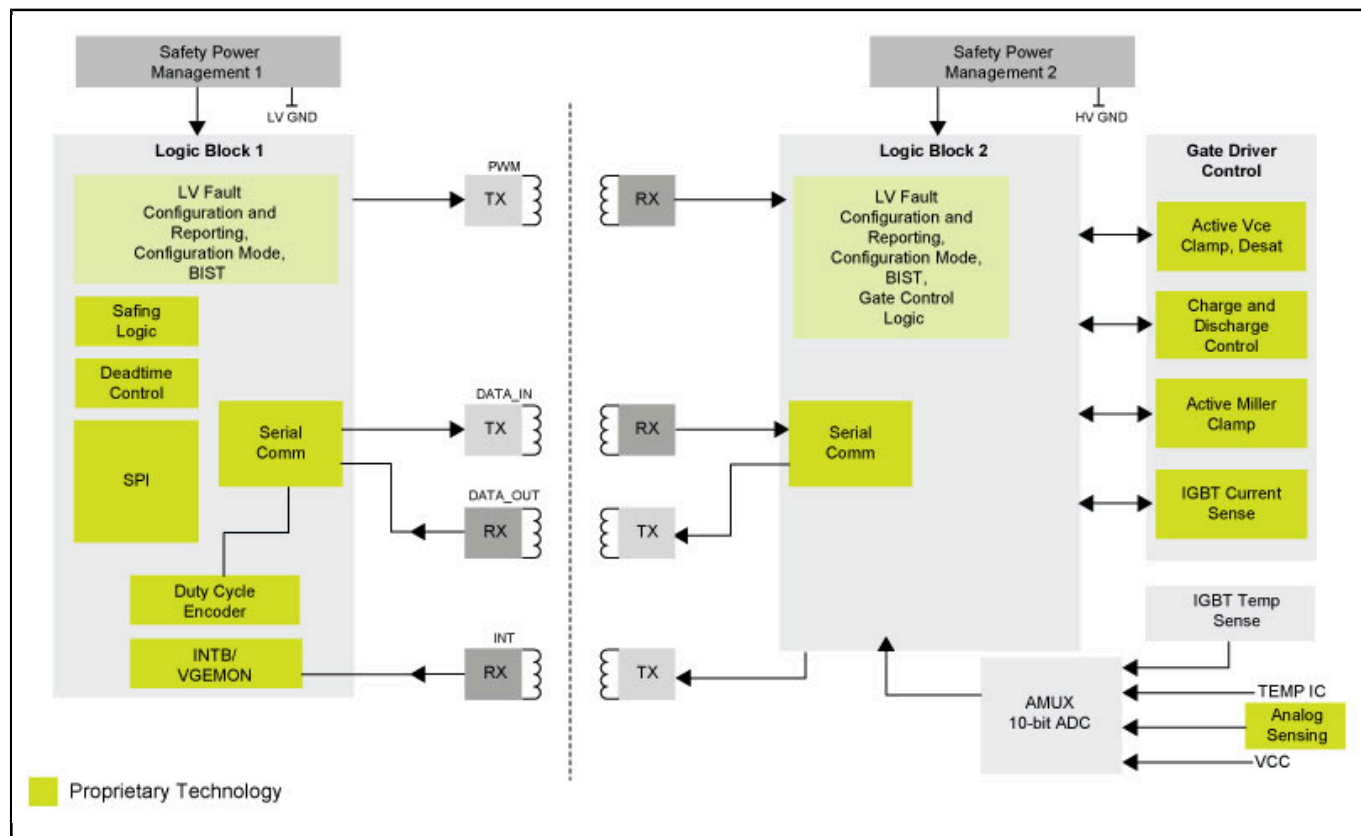
GD3100

Last Updated: Jan 10, 2025

The GD3100 is an advanced single-channel gate driver for IGBTs/SiC. Integrated Galvanic isolation and low on-resistance drive transistors provide high charging and discharging current, low dynamic saturation voltage and rail-to-rail gate voltage control.

- Current and temperature sense minimizes IGBT/SiC stress during faults
- Accurate and configurable under voltage lockout provides protection while ensuring sufficient gate drive voltage headroom
- Autonomously manages severe faults and reports faults and status via INTB pin and an SPI interface. It is capable of directly driving gates of many IGBTs/SiC
- Self-test, control and protection functions are included for the design of high-reliability systems

Advanced High Voltage Isolated Gate Driver for IGBT and SiC MOSFETs Block Diagram



View additional information for [Advanced High Voltage Isolated Gate Driver for IGBT and SiC MOSFETs](#).

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